



GENERAL DESCRIPTION

HC374 is fabricated in the high-speed silicon gate CMOS technology. It has the high noise immunity and low power consumption of standard CMOS integrated circuits. It also offers speeds comparable to low power Schottky devices (LS-TTL).

These 8-bit flip-flops with 3-state outputs are specifically designed for driving highly capacitive or relatively low-impedance loads. They are particularly suitable for implementing buffer registers, I/O ports, bi-directional bus drivers, and working registers.

HC374 has octal positive edge triggered D-type flip-flops. On the positive transition of the clock (CK) input, data at the inputs D, meeting the setup and hold time requirement, are transferred to the Q outputs.

An output-enable input (\overline{OE}) places the eight outputs in either a normal logic state (H or L logic levels) or the high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without interface or pull-up components.

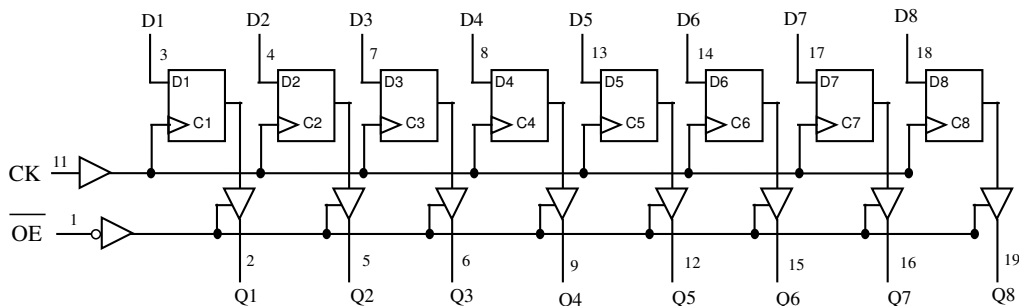
\overline{OE} does not affect the internal operation of the flip-flops. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

\overline{OE} should be tied to VDD through a pull-up resistor to ensure the high-impedance state during power up or power down; the minimum value of the resistor is determined by the current-sinking capability of the driver.

FEATURES

- Wide operating supply voltage range: 2-6V
- Output Drive at VDD = 5V : $\pm 6mA$
- Typical propagation delay: 14ns
- Low input current: $< 1\mu A$
- Low quiescent supply current: 80 μA maximum
- Octal D-type flip-flops in a single package
- Full Parallel access for Loading

LOGIC DIAGRAM



FUNCTIONAL DESCRIPTION**Truth Table**

Inputs			Outputs
$\overline{\text{OE}}$	CK	D	Q
L	↑	H	H
L	↑	L	L
L	H or L	X	Q ₀
H	X	X	Z

H = High Level (steady state). L= Low Level (steady state)

X = Irrelevant (any input, including transitions)

↑ = Transition from low to high level.

Z = high impedance state

Q₀= The level of the output before steady state input conditions were established

ABSOLUTE MAXIMUM RATINGS

Parameter	Value	Unit
DC supply voltage (VDD)	- 0.5 ~ + 7.0	V
DC input or output Voltage (V _{IN} , V _{OUT})	-0.5 to VDD +0.5	V
DC Current Drain per pin, any output (I _{out})	±35	mA
DC Current Drain per pin, VDD or GND (I _{cc})	±70	mA
Storage Temperature(T _{STG})	-65 ~ +150	°C

Note: 1. Absolute maximum ratings are those values beyond which the safety of the device cannot be guaranteed.

RECOMMENDED OPERATING CONDITIONS

Parameter		Min.	Normal	Max.	Unit
DC Supply Voltage (VDD)		2.0	5.0	6.0	V
V _{IH} High-level Input Voltage	VDD=2.0V	1.5			V
	VDD=4.5V	3.15			
	VDD=6.0V	4.2			
V _{IL} Low-level Input Voltage	VDD=2.0V			0.5	V
	VDD=4.5V			1.35	
	VDD=6.0V			1.8	
V _I Input Voltage		0		VDD	V
V _O Output Voltage		0		VDD	V
Operating Temperature (TA)	74HC374	-40		+85	°C
	54HC374	-55		+125	°C
Input Rise/Fall Times (tr, tf)	VDD=2.0V			1000	ns
	VDD=4.5V			500	
	VDD=6.0V			400	

Note: 2. All unused inputs of the device must be held at VDD or GND to ensure proper device operation.

DC ELECTRICAL CHARACTERISTICS

(unless otherwise specified)

Parameter	Test Conditions		VDD	TA =25 °C			54HC374		74HC374		Unit
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
VOH	VI=VIH or VIL	IOH= -20µA	2.0V	1.9	1.998		1.9		1.9	V	
			4.5V	4.4	4.499		4.4		4.4		
			6.0V	5.9	5.999		5.9		5.9		
		4.5V	3.98	4.3		3.7		3.84			
		6.0V	5.48	5.8		5.2		5.34			
VOL	VI=VIH or VIL	IOL = 20µA	2.0V		0.002	0.1		0.1		0.1	V
			4.5V		0.001	0.1		0.1		0.1	
			6.0V		0.001	0.1		0.1		0.1	
		4.5V		0.17	0.26		0.4		0.33		
		6.0V		0.15	0.26		0.4		0.33		
Ii	VI=VDD or 0		6.0V		±0.1	±100		±1000		±1000	nA
IOZ	VO =VDD or 0		6.0V		±0.01	±0.5		±10		±5	µA
Icc	VI=VDD or 0 IO =0		6.0V			8		160		80	µA
Ci			2~6V		3	10		10		10	pF

TIMING REQUIREMENTS OVER RECOMMENDED OPERATING TEMPERATURE RANGE

(unless otherwise noted)

Parameter	VDD	TA =25 °C		54HC374		74HC374		Unit	
		Min.	Max.	Min.	Max.	Min.	Max.		
fclock	Clock frequency	2.0V		6		4		5	MHz
		4.5V		30		20		24	
		6.0V		35		24		28	
tw	Pulse duration, CK high or low	2.0V	80		120		100		ns
		4.5V	16		24		20		
		6.0V	14		20		17		
tsu	Setup time, data before CK↑	2.0V	100		150		125		ns
		4.5V	20		30		25		
		6.0V	17		25		21		
th	Hold time, data after CK↑	2.0V	10		13		12		ns
		4.5V	5		5		5		
		6.0V	5		5		5		

AC ELECTRICAL CHARACTERISTICS (CL = 50pF)

Parameter	From (Input)	To (Output)	VDD	TA =25 °C			54HC374		74HC374		Unit
				Min.	Typ.	Max	Min.	Max.	Min.	Max.	
f _{max}			2.0V	6	12		4		5	MHz	
			4.5V	30	60		20		24		
			6.0V	35	70		24		28		
t _{pd}	CK	Any Q	2.0V		63	180		270		225	ns
			4.5V		17	36		54		45	
			6.0V		15	31		46		38	
t _{en}	$\overline{\text{OE}}$	Any Q	2.0V		60	150		225		190	ns
			4.5V		16	30		45		38	
			6.0V		14	26		38		32	
t _{dis}	$\overline{\text{OE}}$	Any Q	2.0V		36	150		225		190	ns
			4.5V		17	30		45		38	
			6.0V		16	26		38		32	
t _t		Any Q	2.0V		28	60		90		75	ns
			4.5V		8	12		18		15	
			6.0V		6	10		15		13	

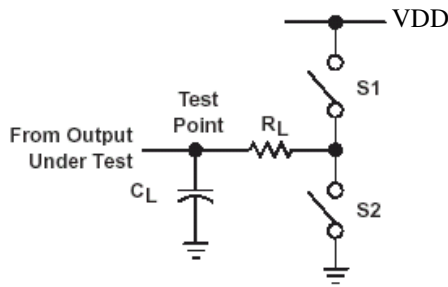
AC ELECTRICAL CHARACTERISTICS (CL = 150pF)

Parameter	From (Input)	To (Output)	VDD	TA =25 °C			54HC374		74HC374		Unit
				Min.	Typ.	Max	Min.	Max.	Min.	Max.	
f _{max}			2.0V	6	12				5	MHz	
			4.5V	30	60				24		
			6.0V	35	70				28		
t _{pd}	CK	Any Q	2.0V		80	230		345		290	ns
			4.5V		22	46		69		58	
			6.0V		19	39		58		49	
t _{en}	$\overline{\text{OE}}$	Any Q	2.0V		70	200		300		250	ns
			4.5V		25	40		60		50	
			6.0V		22	34		51		43	
t _t			2.0V		45	210		315		265	ns
			4.5V		17	42		63		53	
			6.0V		13	36		53		45	

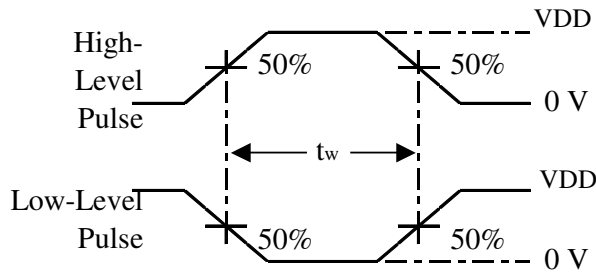
Parameter	Test Conditions	Typ.	Unit
C _{PD} Power Dissipation Capacitance	TA =25 °C , No Load	100	pF

Note 3: C_{PD} determines the no load dynamic power consumption , $P_D = C_{PD} \cdot V_{DD}^2 \cdot f + I_{CC} \cdot V_{DD}$, and the no load dynamic current consumption, $I_S = C_{PD} \cdot V_{DD} \cdot f_i + I_{CC}$

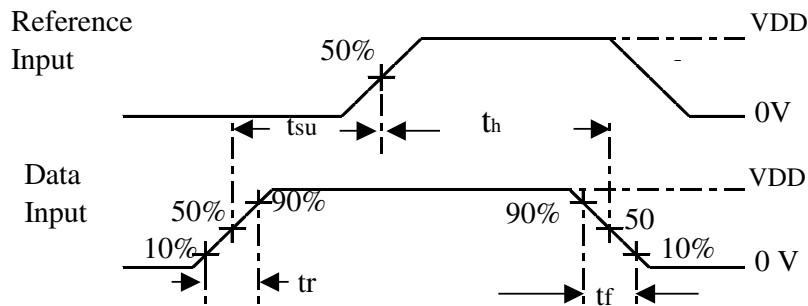
AC TEST CIRCUIT AND AC SWITCHING WAVEFORM



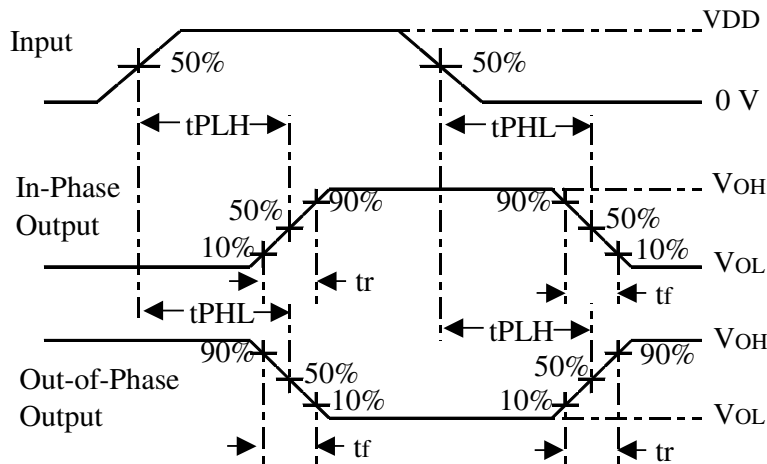
PARAMETER		RL	CL	S1	S2
ten	t _{PZH}	1kΩ	50pF or	Open	Closed
	t _{PZL}		150pF	Closed	Open
tdis	t _{PHZ}	1kΩ	50pF	Open	Closed
	t _{PLZ}			Closed	Open
tpd or t _t		---	50pF or 150pF	Open	Open



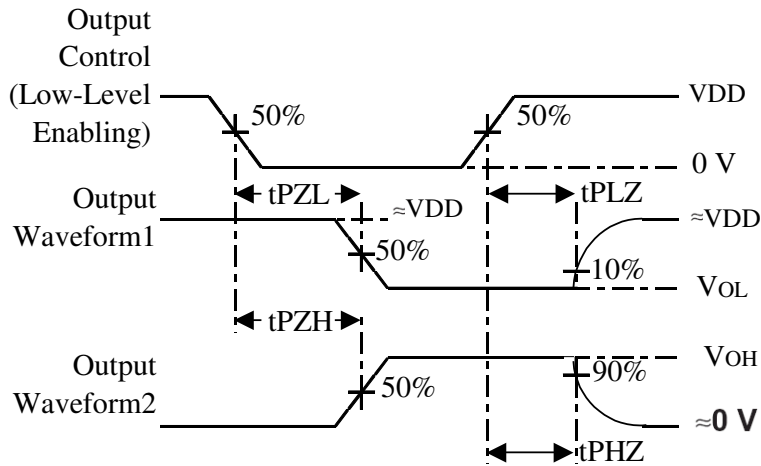
Voltage Waveforms
Pulse Durations



Voltage Waveforms
Setup and Hold and Input rise and Fall times



Voltage Waveforms
Propagation Delay and Output Transition Times



Voltage Waveforms

Enable and disable times for 3-state outputs

NOTES 4: 1) C_L includes probe and test-fixture capacitance.

2) Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control.

Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.

3) Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics:

PRR δ 1 MHz, $Z_O = 50\Omega$., $t_r = 6$ ns, $t_f = 6$ ns.

4) For clock inputs, f_{max} is measured when the input duty cycle is 50%.

5) The outputs are measured one at a time with one input transition per measurement.

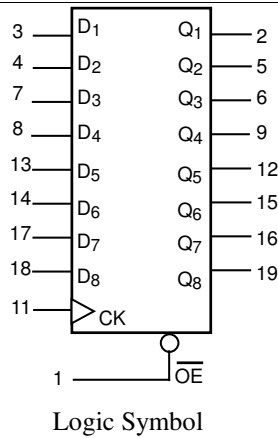
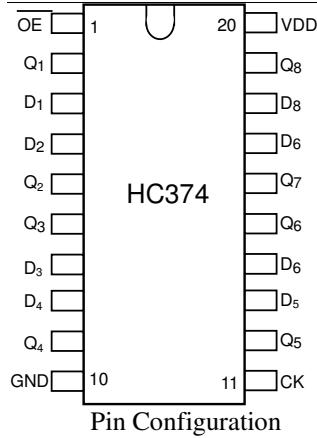
6) t_{PLZ} and t_{PHZ} are the same as t_{dis} .

7) t_{PZL} and t_{PZH} are the same as t_{en} .

8) t_{PLH} and t_{PHL} are the same as t_{pd} .

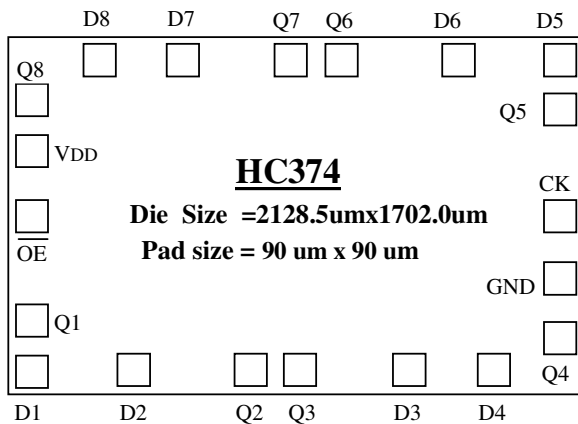
PIN DESCRIPTION

PIN NO.	SYMBOL	DESCRIPTION
3, 4, 7, 8, 13, 14, 17, 18	D1– D8	Data Inputs
2, 5, 6, 9, 12, 15, 18, 19	Q1 – Q8	Outputs
10	GND	Ground (0V)
11	CK	Clock input (active at rising edge)
1	\overline{OE}	Output Enable
20	VDD	Positive power supply



PAD DIAGRAM

The Coordinate of Each Pad



Q1 (-779.8, -337.8)	Q5 (689.5, 247.7)
D1 (-779.8, -977.7)	D5 (689.5, 387.7)
D2 (-496.0, -977.7)	D6 (405.7, 387.7)
Q2 (-171.0, -977.7)	Q6 (80.7, 387.7)
Q3 (-31.0, -977.7)	Q7 (-59.3, 387.7)
D3 (273.5, -977.7)	D7 (-363.8, 387.7)
D4 (502.3, -977.7)	D8 (-592.6, 387.7)
Q4 (689.5, -385.7)	Q8 (-779.8, 274.1)
GND (689.5, -224.1)	VDD (-779.8, 134.1)
CK (689.5, -45.1)	OE (-779.8, -44.9)

Note: Substrate should be connected to VDD or left it open.

PAD IDENTIFICATION

